

(12) **United States Patent**
Harari et al.

(10) **Patent No.:** **US 6,523,132 B1**
 (45) **Date of Patent:** **Feb. 18, 2003**

(54) **FLASH EEPROM SYSTEM**

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 (*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.
 (21) Appl. No.: **09/657,482**
 (22) Filed: **Sep. 8, 2000**

Related U.S. Application Data

- (60) Continuation of application No. 08/789,421, filed on Jan. 29, 1997, now Pat. No. 6,149,316, which is a continuation of application No. 08/174,768, filed on Dec. 29, 1993, now Pat. No. 5,602,987, which is a continuation of application No. 07/963,838, filed on Oct. 20, 1992, now Pat. No. 5,297,148, which is a division of application No. 07/337,566, filed on Apr. 13, 1989, now abandoned.
 (51) **Int. Cl.**⁷ **G06F 11/00**
 (52) **U.S. Cl.** **714/8; 714/723; 714/710**
 (58) **Field of Search** **714/8, 723, 710; 365/185.16, 185.25, 185.02, 230.06**

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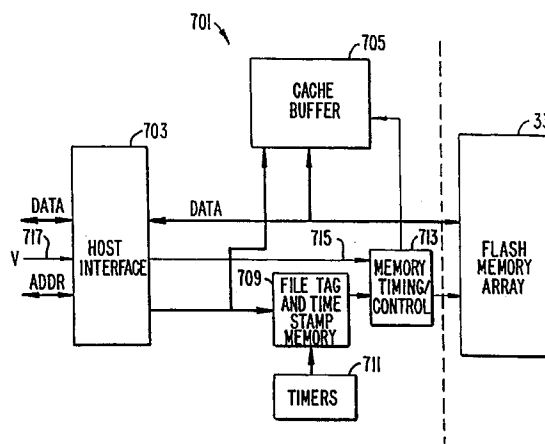
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(57) **ABSTRACT**

A system of Flash EEprom memory chips with controlling circuits serves as non-volatile memory such as that provided by magnetic disk drives. Improvements include selective multiple sector erase, in which any combinations of Flash sectors may be erased together. Selective sectors among the selected combination may also be de-selected during the erase operation. Another improvement is the ability to remap and replace defective cells with substitute cells. The remapping is performed automatically as soon as a defective cell is detected. When the number of defects in a Flash sector becomes large, the whole sector is remapped. Yet another improvement is the use of a write cache to reduce the number of writes to the Flash EEprom memory, thereby minimizing the stress to the device from undergoing too many write/erase cycling.

27 Claims, 5 Drawing Sheets



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